3.3 V 16-bit transceiver; 3-state Rev. 07 — 29 March 2010

Product data sheet

1. General description

The 74LVT16245B; 74LVTH16245B is a high-performance BiCMOS product designed for V_{CC} operation at 3.3 V.

This device is a 16-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The control function implementation minimizes external timing requirements. The device features an output enable input (nOE) for easy cascading and a direction input (nDIR) for direction control.

2. Features and benefits

- 16-bit bidirectional bus interface
- 3-state buffers
- Output capability: +64 mA and -32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Bus hold data inputs eliminate need for external pull-up resistors to hold unused inputs
- Live insertion and extraction permitted
- Power-up 3-state
- No bus current loading when output is tied to 5 V bus
- Latch-up protection:
 - JESD78B Class II exceeds 500 mA
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V

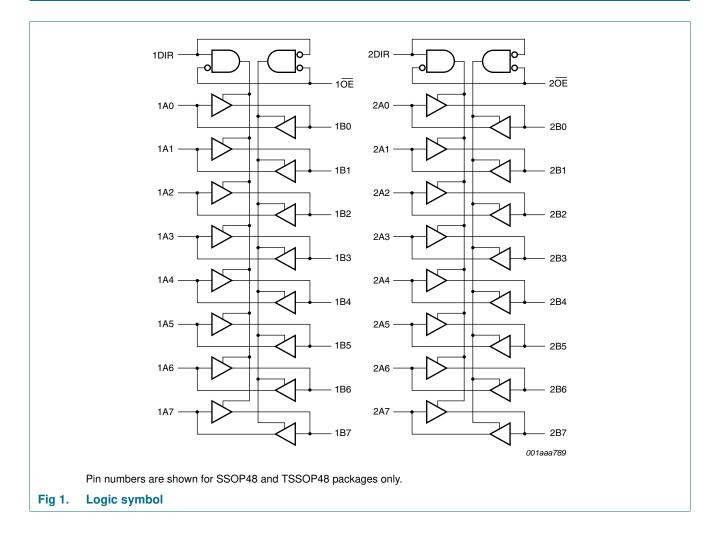


3.3 V 16-bit transceiver; 3-state

Ordering information 3.

Type number	Package						
	Temperature range	Name	Description	Version			
74LVT16245BDL	–40 °C to +85 °C	SSOP48	plastic shrink small outline package; 48 leads;	SOT370-1			
74LVTH16245BDL			body width 7.5 mm				
74LVT16245BDGG	–40 °C to +85 °C	TSSOP48	plastic thin shrink small outline package; 48 leads; body width 6.1 mm	SOT362-1			
74LVTH16245BDGG							
74LVT16245BEV	–40 °C to +85 °C	VFBGA56	plastic very thin fine-pitch ball grid array package; 56 balls; body $4.5\times7\times0.65~mm$	SOT702-1			
74LVT16245BBQ	–40 °C to +85 °C	HXQFN60U	plastic thermal enhanced extremely thin quad flat	SOT1134-1			
74LVTH16245BBQ			package; no leads; 60 terminals; UTLP based; body $4 \times 6 \times 0.5$ mm				

Functional diagram 4.

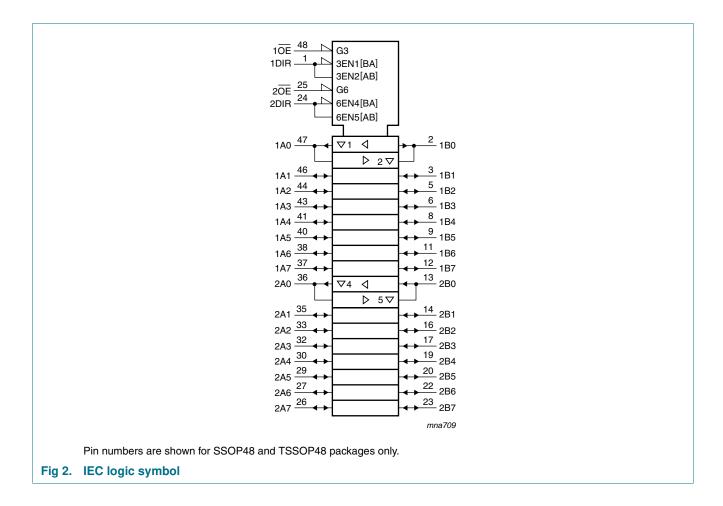


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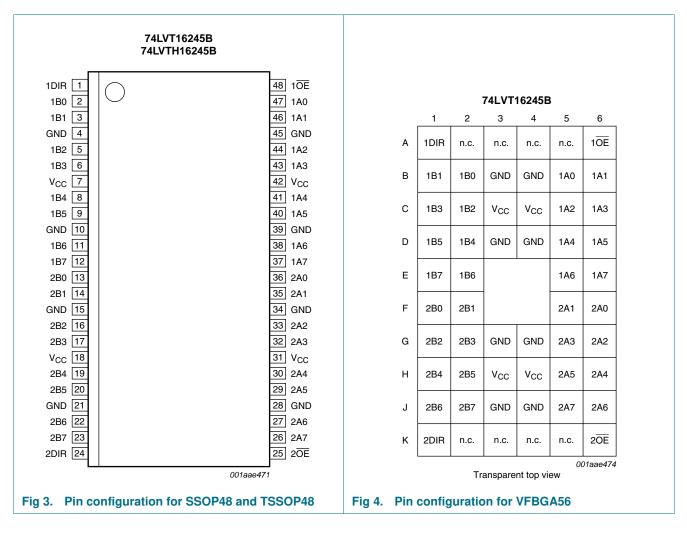
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5. Pinning information

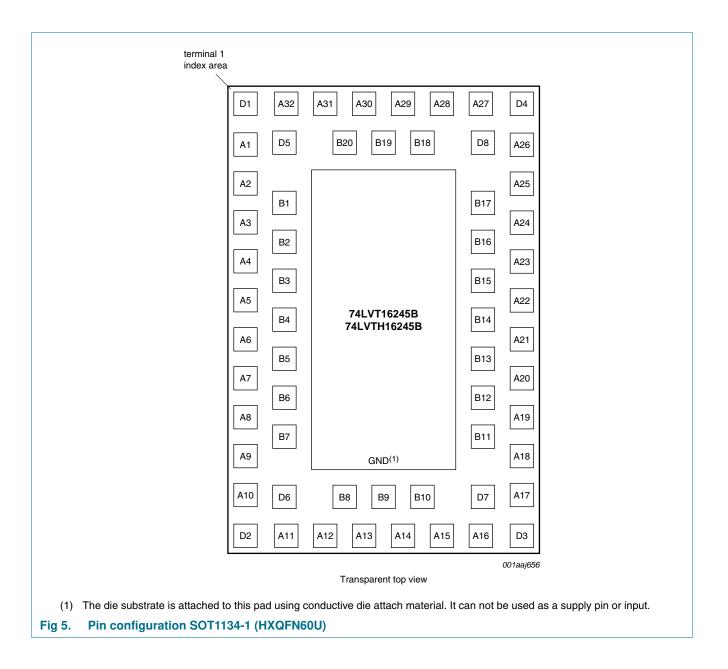
5.1 Pinning



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5.2 Pin description

Symbol	Pin			Description
	SOT370-1 and SOT362-1	SOT702-1	SOT1134-1	-
1DIR, 2DIR	1, 24	A1, K1	A30, A13	direction control input
1B0 to 1B7	2, 3, 5, 6, 8, 9, 11, 12	B2, B1, C2, C1, D2, D1, E2, E1	B20, A31, D5, D1, A2, B2, B3, A5	data input/output
2B0 to 2B7	13, 14, 16, 17, 19, 20, 22, 23	F1, F2, G1, G2, H1, H2, J1, J2	A6, B5, B6, A9, D2, D6, A12, B8	data input/output
GND	4, 10, 15, 21, 28, 34, 39, 45	B3, D3, G3, J3, J4, G4, D4, B4	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)
V _{CC}	7, 18, 31, 42	C3, H3, H4, C4	A1, A10, A17, A26	supply voltage
1 <u>0E</u> , 2 <u>0E</u>	48, 25	A6, K6	A29, A14	output enable input (active LOW)
2A0 to 2A7	36, 35, 33, 32, 30, 29, 27, 26	F6, F5, G6, G5, H6, H5, J6, J5	A21, B13, B12, A18, D3, D7, A15, B10	data input/output
1A0 to 1A7	47, 46, 44, 43, 41, 40, 38, 37	B5, B6, C5, C6, D5, D6, E5, E6	B18, A28, D8, D4, A25, B16, B15, A22	data input/output
n.c.	-	A2, A3, A4, A5, K2, K3, K4, K5	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected

6. Functional description

6.1 Function table

Function table [1] Table 3.

		Input/output		
n <mark>OE nDIR r</mark>		nAn	nBn	
L	L	output nAn = nBn	input	
L	Н	input	output nBn = nAn	
Н	Х	Z	Z	

[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care;

Z = high-impedance OFF-state.

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					-
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
VI	input voltage		<u>[1]</u> –0.5	+7.0	V
Vo	output voltage	output in OFF-state or HIGH-state	<u>[1]</u> –0.5	+7.0	V
I _{IK}	input clamping current	V ₁ < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
lo	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-64	-	mA
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		[2] _	150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \text{ °C to } +85 \text{ °C};$			
		(T)SSOP48 package	<u>[3]</u> _	500	mW
		VFBGA56 package	<u>[4]</u> -	1000	mW
		HXQFN60U package	<u>[4]</u> -	1000	mW

[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

[3] Above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

[4] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{CC}	supply voltage		2.7	-	3.6	V
VI	input voltage		0	-	5.5	V
V _{IH}	HIGH-level input voltage		2.0	-	-	V
V _{IL}	LOW-level input voltage		-	-	0.8	V
I _{OH}	HIGH-level output current		-32	-	-	mA
I _{OL}	LOW-level output current	none	-	-	32	mA
		current duty cycle \leq 50 %; $f_i \geq$ 1 kHz	-	-	64	mA
T _{amb}	ambient temperature	in free-air	-40	-	+85	°C
$\Delta t / \Delta V$	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

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9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
T _{amb} = -	40 °C to +85 °C <u>[1]</u>					
V _{IK}	input clamping voltage	V_{CC} = 2.7 V; I_{IK} = -18 mA	-1.2	-0.85	-	V
V _{OH}	HIGH-level output voltage	I_{OH} = $-100~\mu A;~V_{CC}$ = 2.7 V to 3.6 V	$V_{CC} - 0.2$	2 V _{CC}	-	V
		$I_{OH} = -8 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.4	2.5	-	V
		$I_{OH} = -32 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	2.3	-	V
V _{OL}	LOW-level output voltage	$V_{CC} = 2.7 V$				
		I _{OL} = 100 μA	-	0.07	0.2	V
		I _{OL} = 24 mA	-	0.3	0.5	V
		$V_{CC} = 3.0 V$				
		I _{OL} = 16 mA	-	0.25	0.4	V
		I _{OL} = 32 mA	-	0.3	0.5	V
		I _{OL} = 64 mA	-	0.4	0.55	V
l _l	input leakage current	control pins				
		V_{CC} = 3.6 V; V_{I} = V_{CC} or GND	-	0.1	±1	μA
		$V_{CC} = 0 \text{ V or } 3.6 \text{ V}; \text{ V}_{I} = 5.5 \text{ V}$	-	0.1	10	μA
		input/output data pins; $V_{CC} = 3.6 V$	[2]			
		V ₁ = 5.5 V	-	0.1	20	μA
		$V_I = V_{CC}$	-	0.5	10	μA
		$V_{I} = 0 V$	-5	-0.1	-	μA
I _{OFF}	power-off leakage current	V_{CC} = 0 V; V _I or V_O = 0 V to 4.5 V	-	0.1	±100	μA
I _{BHL}	bus hold LOW current	$V_{CC} = 3 \text{ V}; \text{ V}_{I} = 0.8 \text{ V}$	<u>3</u> 75	135	-	μA
I _{BHH}	bus hold HIGH current	$V_{CC} = 3 \text{ V}; \text{ V}_{I} = 2.0 \text{ V}$	-	-135	-75	μA
I _{BHLO}	bus hold LOW overdrive current	nAn input; V _I = 0 V to 3.6 V; V _{CC} = 3.6 V	500	-	-	μA
I _{BHHO}	bus hold HIGH overdrive current	nAn input; V _I = 0 V to 3.6 V; V _{CC} = 3.6 V	-	-	-500	μA
I _{LO}	output leakage current	output in HIGH-state when $V_O > V_{CC}$; $V_O = 5.5 V$; $V_{CC} = 3.0 V$	-	75	125	μA
I _{O(pu/pd)}	power-up/power-down output current	$V_{CC} \leq \underline{1.2}~V;~V_O$ = 0.5 V to $V_{CC};~V_I$ = GND or $V_{CC};~n\overline{OE}$ = don't care	<u>[4]</u> _	40	±100	μA
I _{CC}	supply current	V_{CC} = 3.6 V; V_I = GND or V_{CC} ; I_O = 0 A				
		outputs HIGH	-	0.07	0.12	mA
		outputs LOW	-	4.7	6.0	mA
		outputs disabled	<u>[5]</u>	0.07	0.12	mA
ΔI_{CC}	additional supply current	per input pin; $V_{CC} = 3.0$ V to 3.6 V; one input at $V_{CC} - 0.6$ V, other inputs at V_{CC} or GND	<u>[6]</u>	0.1	0.2	mA
CI	input capacitance	pins nDIR and nOE, $V_0 = 0$ V or 3.0 V	-	3	-	pF

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).								
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
$C_{io(off)}$	off-state input/output capacitance	pins nAn and nBn, outputs disabled; V_{O} = GND or V_{CC}	-	9	-	pF		

Table 6. Static characteristics ...continued

[1] Typical values are measured at V_{CC} = 3.3 V and at T_{amb} = 25 °C.

[2] Unused pins at V_{CC} or GND.

[3] This is the bus hold overdrive current required to force the input to the opposite logic state.

[4] This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.3 V \pm 0.3 V a transition time of 100 μ s is permitted. This parameter is valid for T_{amb} = 25 °C only.

[5] I_{CC} is measured with outputs pulled to V_{CC} or GND.

[6] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

Table 7.Dynamic characteristics

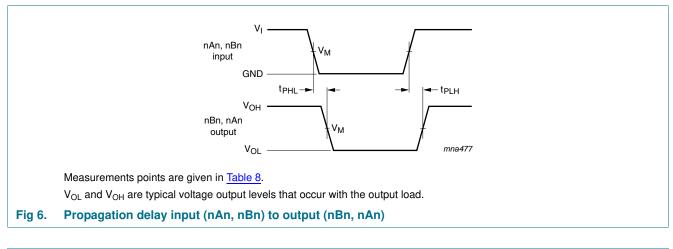
Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit		
T _{amb} = -4	T _{amb} = −40 °C to +85 °C							
t _{PLH}	LOW to HIGH propagation delay	nAn to nBn or nBn to nAn; see <u>Figure 6</u>						
		$V_{CC} = 2.7 V$	-	-	3.5	ns		
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	1.9	3.3	ns		
t _{PHL}	HIGH to LOW propagation delay	nAn to nBn or nBn to nAn; see <mark>Figure 6</mark>						
		$V_{CC} = 2.7 V$	-	-	3.5	ns		
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	1.7	3.3	ns		
t _{PZH} O	OFF-state to HIGH propagation delay	nOE to nAn or nBn; see Figure 7						
		$V_{CC} = 2.7 V$	-	-	5.3	ns		
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	2.8	4.5	ns		
t _{PZL}	OFF-state to LOW	nOE to nAn or nBn; see <u>Figure 7</u>						
	propagation delay	$V_{CC} = 2.7 V$	-	-	5.1	ns		
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	1.0	2.8	4.1	ns		
t _{PHZ}	HIGH to OFF-state	nOE to nAn or nBn; see <u>Figure 7</u>						
	propagation delay	$V_{CC} = 2.7 V$	-	-	5.7	ns		
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.5	3.2	5.1	ns		
t _{PLZ}	LOW to OFF-state	nOE to nAn or nBn; see <u>Figure 7</u>						
	propagation delay	$V_{CC} = 2.7 V$	-	-	4.6	ns		
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.5	3.0	4.6	ns		

[1] All typical values are at V_{CC} = 3.3 V and T_{amb} = 25 °C.

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11. Waveforms



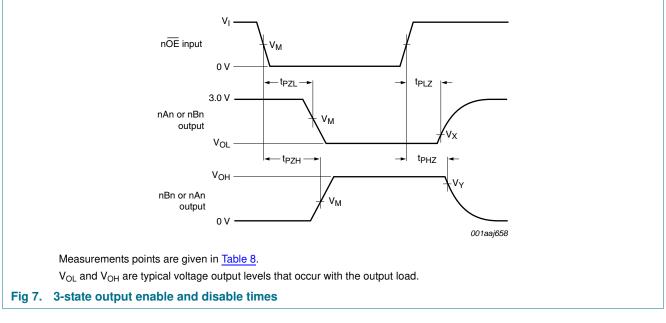


Table 8.Measurement points

Input	Output		
V _M	V _M	V _X	V _Y
1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V

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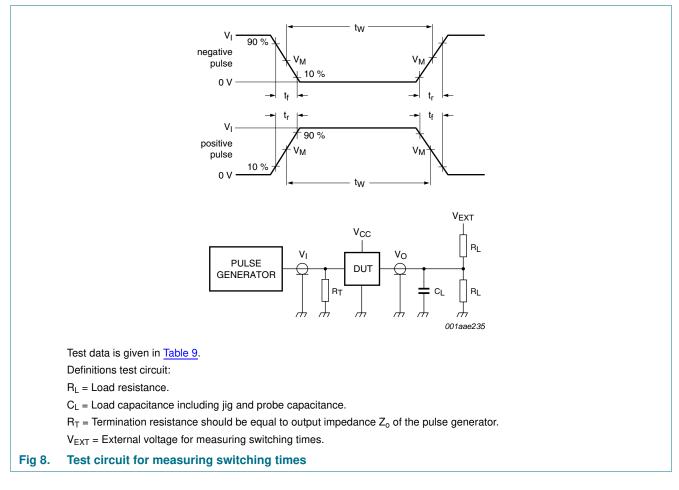


Table 9. Test data

Input				Load		V _{EXT}		
VI	f _i	tw	t _r , t _f	CL	RL	t _{PHZ} , t _{PZH}	t _{PLZ} , t _{PZL}	t _{PLH} , t _{PHL}
2.7 V	\leq 10 MHz	500 ns	≤ 2.5 ns	50 pF	500 Ω	GND	6 V	open

3.3 V 16-bit transceiver; 3-state

12. Package outline

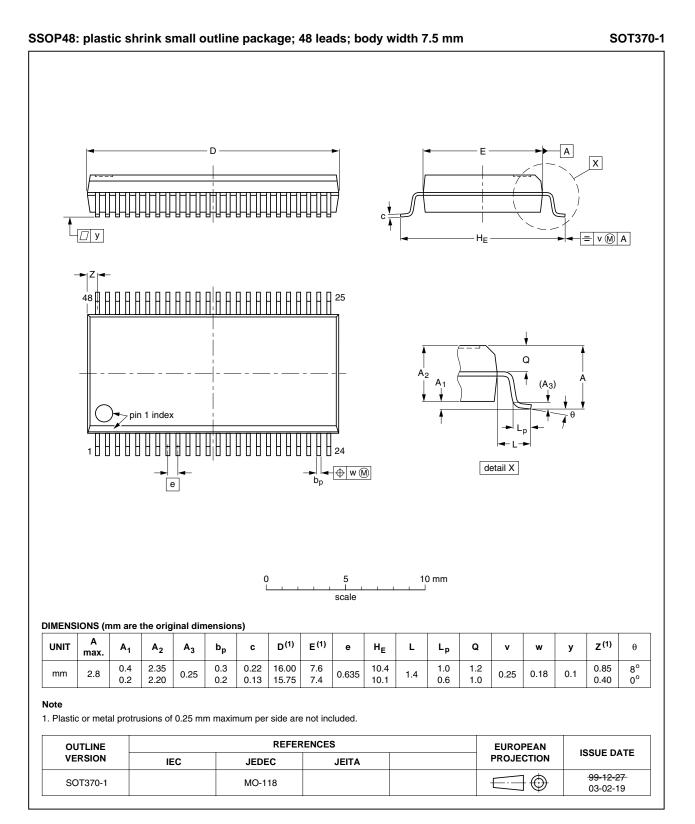


Fig 9. Package outline SOT370-1 (SSOP48)

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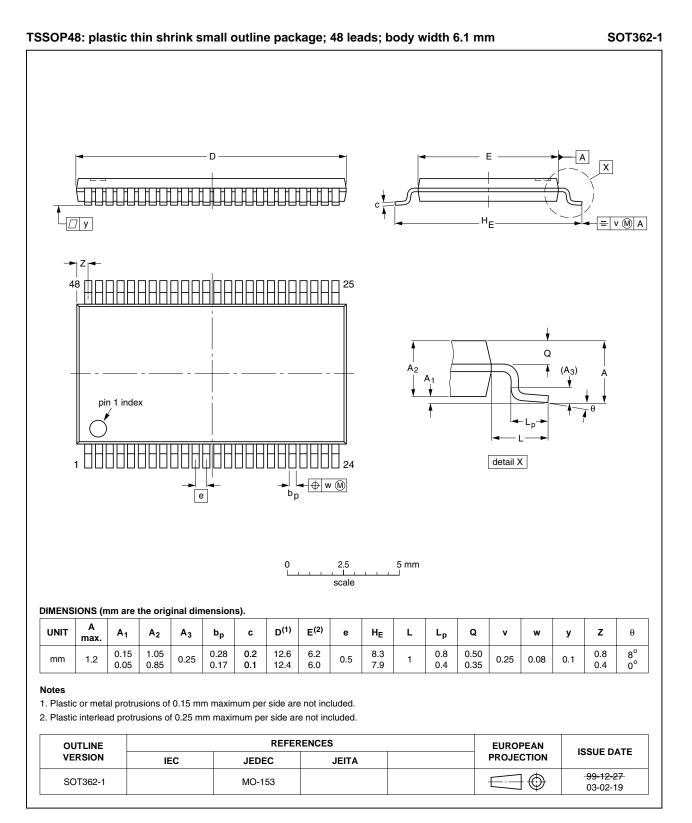
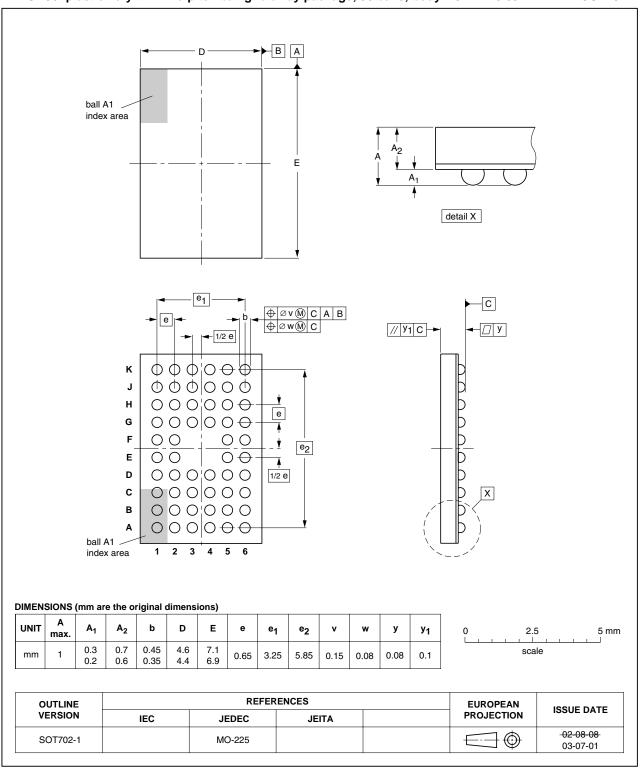


Fig 10. Package outline SOT362-1 (TSSOP48)

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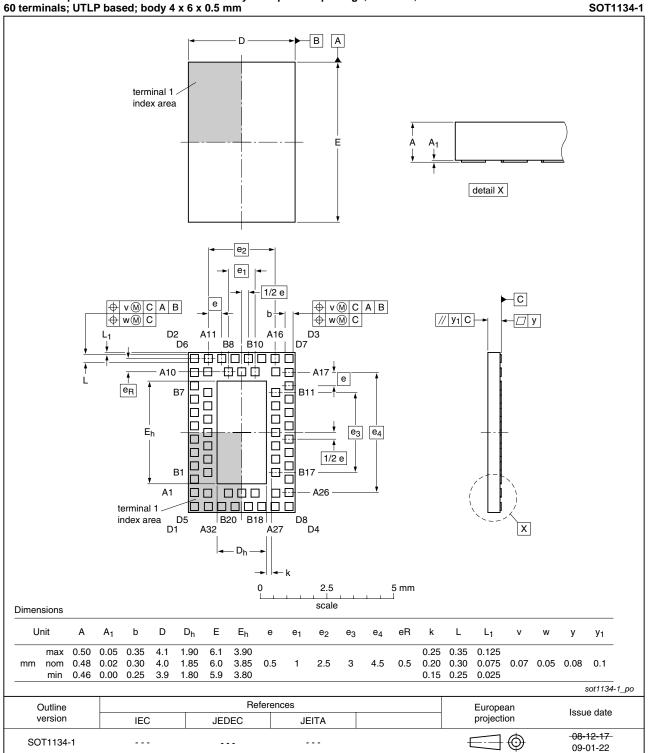


VFBGA56: plastic very thin fine-pitch ball grid array package; 56 balls; body 4.5 x 7 x 0.65 mm SOT702-1

Fig 11. Package outline SOT702-1 (VFBGA56)

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HXQFN60U: plastic thermal enhanced extremely thin quad flat package; no leads; 60 terminals; UTLP based; body 4 x 6 x 0.5 mm

Fig 12. Package outline SOT1134-1 (HXQFN60U)

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13. Abbreviations

Table 10.	Abbreviations
Acronym	Description
BiCMOS	Bipolar Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVT_LVTH16245B_7	20100329	Product data sheet	-	74LVT_LVTH16245B_6
Modifications: • 74LVT16245BBQ and 74LVTH16245BBQ changed from HUQFN60U (SOT1025-1 HXQFN60U (SOT1134-1) package.				
74LVT_LVTH16245B_6	20090409	Product data sheet	-	74LVT_LVTH16245B_5
Modifications:	<u>Section 2</u> : C	lass II added for latch-up prote	ction.	
	 <u>Table 6</u>: Cor 	ditions for bus hold overdrive o	current have change	d.
74LVT_LVTH16245B_5	20090312	Product data sheet	-	74LVT_LVTH16245B_4
74LVT_LVTH16245B_4	20060323	Product data sheet	-	74LVT16245B_3
74LVT16245B_3	20021031	Product data sheet	-	74LVT16245B_2
74LVT16245B_2	19980219	Product specification	-	74LVT16245B_1
74LVT16245B_1	19940523	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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